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				Application Number	
				Filing Date	
				First Named Inventor	Thomas M. Crawford
				Group Art Unit	
				Examiner Name	
Sheet	1	of	1	Attorney Docket Number	SEAG 63445

U.S. PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
92		4,446,425		Valdmanis et al.	05-01-1984	
		4,482,863		Auston et al.	11-13-1984	
		6,081,499		Berger et al.	06-27-2000	
		6,134,207		Jerman et al.	10-17-2000	
		6,463,190		Kato et al.	10-08-2002	
92		Publication No. 2003/0053258		Dunn et al.	03-20-2003	

FOREIGN PATENT DOCUMENTS								
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				Group Art Unit	
				Examiner Name	
Sheet	1	of	1	Attorney Docket Number	SEAG 63445

Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
g2		D. H. AUSTON, "Picosecond Optoelectronic Switching and Gating in Silicon," <i>Applied Physics Letters</i> , Vol. 26, No. 3, February 1, 1975, pp. 101-103.	
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		G. BURNS, <i>Solid State Physics</i> , Academic Press, San Diego, 1985, pp. 288-289.	
		F. E. DOANY ET AL., "Carrier Lifetime Versus Ion-Implantation Dose in Silicon on Sapphire," <i>Applied Physics Letters</i> , Vol. 50, No. 8, February 23, 1987, pp. 460-462.	
		M. E. DUNHAM ET AL., "Saturation Behavior of Silicon Auston Switches," <i>Journal of Applied Physics</i> , Vol. 66, No. 1, July 1, 1989, pp. 413-418.	
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		U. D. KEIL ET AL., "Generation of Ultrashort Electrical Pulses With Variable Pulse Widths," <i>Applied Physics Letters</i> , Vol. 66, No. 13, March 27, 1995, pp. 1629-1631.	
		R. G. DECORBY ET AL., "Large (50 μm) ² Metal-Semiconductor-Metal Photodetectors With 18 GHz Bandwidth at 3 V Bias; Reduction of Hole Pileup," <i>Applied Physics Letters</i> , Vol. 73, No. 2, July 13, 1998, pp. 196-198.	
g2		M. STELLMACHER ET AL., "Photoconductivity Investigation of the Electron Dynamics in GaAs Grown at Low Temperature," <i>Applied Physics Letters</i> , Vol. 74, No. 9, March 1, 1999, pp. 1239-1241.	

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